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TEMPERATURE-DEPENDENCE OF CHARGE TRANSPORT IN SINGLE-CRYSTAL EUB6

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Authors

VONMOLNAR, S GUY, CN ETOURNEAU, J <u>et al.</u>

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BM 10 Temperature Dependence of Charge Transport in Single Crystal EuB6. S. VON MOLNAR, C. N. GUY+, J. ETOURNEAU++, IBM T. J. Watson Res. Cntr., Yorktown Heights, NY 10598 and Z. FISK, U.C. San Diego, La Jolla, CA 92093--We present Hall and resistivity data which demonstrate that EuB₆ is a degenerate semiconductor transforming into a metal or semimetal below the ferromagnetic ordering temperature $(T_c=13.7K)$. We find that there is a factor 5 decrease in the normal Hall coefficient as temperature is decreased to 4.2K. A simple one band model leads to the following: neff $(150K) = 3.5 \times 10^{19} cm^{-3}$ and $n_{eff}(4.2K) = 1.7 \times 10^{20} cm^{-3};$ $\mu_{eff}(150K) \simeq 300 \text{ cm}^2/\text{vsec.}$, whereas $\mu_{eff}(4.2K) = 2560 \text{ cm}^2/\text{vsec.}$ We interpret these data as arising from a magnetically driven electronic phase transition in which the strong coupling between conduction electrons and localized 4f spins determine the conduction band position.

⁺Permanent Address: Blackett Laboratory, Imperial College, London SW7 2BZ

⁺⁺Permanent Address: Laboratoire de Chimie du Solide du CNRS, U. Bordeaux I, 33405 Talence Cedex, France.